September 2013



FSBS15CH60F Motion SPM[®] 3 Series

Features

- UL Certified No.E209204(SPMBA-027 Package)
- 600 V-15 A 3 Phase IGBT Inverter Bridge Including Control ICs for Gate Driving and Protection
- Three Separate Negative DC-link Terminals for Inverter Current Sensing
- Single-Grounded Power Supply for Built-In HVICs
- Isolation Rating of 2500 Vrms/min.
- Low Thermal Resistance by Using Ceramic Substarte

RoHS compliant Applications

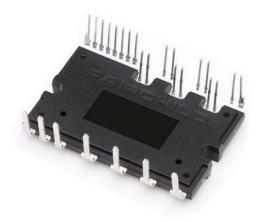
 Motion Control - Home Appliance / Industrial Motor Features

General Description

FSBS15CH60F Is A Motion SPM® 3 Series that Fairchild Has Developed to Provide A Very Compact and High Performance Inverter Solution for AC Motor Drives in Low-Power Applications Such as Air Conditioners and Washing Machines. It Combines Optimized Circuit Protections and Drives Matched to Low-Loss IGBTs. The System Reliability Is Further Enhanced by The Integrated Under-Voltage Lock-Out and Over-Current Protection. The High Speed Built-In HVIC Provides Optocoupler-Less Single-Supply IGBT Gate Driving Capability that Further Reduces The Overall Size of The Inverter System. Each Phase Leg Current of The Inverter Can Be Monitored Thanks to Three Separate Negative DC Terminals.

Resource

• AN-9035: Motion SPM® 3 Series Ver.2 User's Guide





Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Packing Type	Quantity
FSBS15CH60F	FSBS15CH60F	SPMBA-027	-	RAIL	10

Integrated Power Functions

• 600 V - 15 A IGBT Inverter for Three-Phase DC/AC Power Conversion (Please Refer to Figure 3)

Integrated Drive, Protection and System Control Functions

- For Inverter High-Side IGBTs: Gate Drive Circuit, High Voltage Isolated High-Speed Level Shifting
 Control Circuit Under-Voltage (UV) Protection
 Note) Available Bootstrap Circuit Example is Given in Figures 10 and 11.
- For Inverter Low-Side IGBTs: Gate Drive Circuit, Short Circuit Protection (SC)
 Control Supply Circuit Under-Voltage (UV) Protection
- Fault Sgnaling: Corresponding to a UV Fault (Low-Side Supply)
- Input interface: Active High Interface, Can Work with 3.3 / 5 V Logic

Pin Configuration

Top View

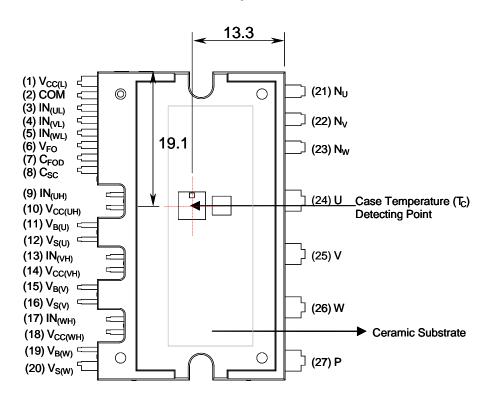
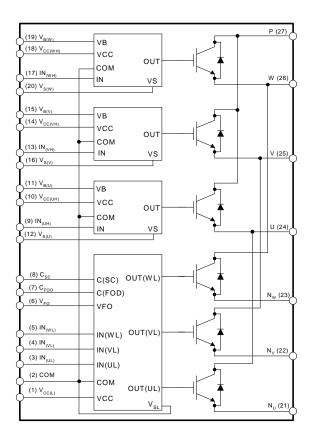


Figure 2.

Pin Descriptions

Pin Number	Pin Name	Pin Description
1	V _{CC(L)}	Low-side Common Bias Voltage for IC and IGBTs Driving
2	СОМ	Common Supply Ground
3	IN _(UL)	Signal Input for Low-side U Phase
4	IN _(VL)	Signal Input for Low-side V Phase
5	IN _(WL)	Signal Input for Low-side W Phase
6	V _{FO}	Fault Output
7	C _{FOD}	Capacitor for Fault Output Duration Time Selection
8	C _{SC}	Capacitor (Low-pass Filter) for Short-Current Detection Input
9	IN _(UH)	Signal Input for High-side U Phase
10	V _{CC(UH)}	High-side Bias Voltage for U Phase IC
11	V _{B(U)}	High-side Bias Voltage for U Phase IGBT Driving
12	V _{S(U)}	High-side Bias Voltage Ground for U Phase IGBT Driving
13	IN _(VH)	Signal Input for High-side V Phase
14	V _{CC(VH)}	High-side Bias Voltage for V Phase IC
15	V _{B(V)}	High-side Bias Voltage for V Phase IGBT Driving
16	V _{S(V)}	High-side Bias Voltage Ground for V Phase IGBT Driving
17	IN _(WH)	Signal Input for High-side W Phase
18	V _{CC(WH)}	High-side Bias Voltage for W Phase IC
19	V _{B(W)}	High-side Bias Voltage for W Phase IGBT Driving
20	V _{S(W)}	High-side Bias Voltage Ground for W Phase IGBT Driving
21	N _U	Negative DC-Link Input for U Phase
22	N _V	Negative DC-Link Input for V Phase
23	N _W	Negative DC-Link Input for W Phase
24	U	Output for U Phase
25	V	Output for V Phase
26	W	Output for W Phase
27	Р	Positive DC-Link Input

Internal Equivalent Circuit and Input/Output Pins



Note

- 1. Inverter low-side is composed of three IGBTs, freewheeling diodes for each IGBT and one control IC. It has gate drive and protection functions.
- 2. Inverter power side is composed of four inverter dc-link input terminals and three inverter output terminals.
- 3. Inverter high-side is composed of three IGBTs, freewheeling diodes and three drive ICs for each IGBT.

Figure 3.

Absolute Maximum Ratings (T_J = 25°C, Unless Otherwise Specified)

Inverter Part

Symbol	Parameter	Conditions	Rating	Unit
V _{PN}	Supply Voltage	Applied between P- N _U , N _V , N _W	450	V
V _{PN(Surge)}	Supply Voltage (Surge)	Applied between P- N _U , N _V , N _W	500	V
V _{CES}	Collector-emitter Voltage		600	V
± I _C	Each IGBT Collector Current	T _C = 25°C	15	А
± I _{CP}	Each IGBT Collector Current (Peak)	T _C = 25°C, Under 1ms Pulse Width	30	Α
P _C	Collector Dissipation	T _C = 25°C per One Chip	32	W
T _J	Operating Junction Temperature	(Note 1)	-20 ~ 125	°C

Note

Control Part

Symbol	Parameter	Conditions	Rating	Unit
V _{CC}	Control Supply Voltage	Applied between $V_{CC(UH)}$, $V_{CC(VH)}$, $V_{CC(WH)}$, $V_{CC(L)}$ - COM	20	V
V _{BS}	High-side Control Bias Voltage	Applied between $V_{B(U)}$ - $V_{S(U)}$, $V_{B(V)}$ - $V_{S(V)}$, $V_{B(W)}$ - $V_{S(W)}$	20	V
V _{IN}	Input Signal Voltage	Applied between $IN_{(UH)}$, $IN_{(VH)}$, $IN_{(WH)}$, $IN_{(UL)}$, $IN_{(VL)}$, $IN_{(VL)}$, $IN_{(WH)}$	-0.3~17	V
V _{FO}	Fault Output Supply Voltage	Applied between V _{FO} - COM	-0.3~V _{CC} +0.3	V
I _{FO}	Fault Output Current	Sink Current at V _{FO} Pin	5	mA
V_{SC}	Current Sensing Input Voltage	Applied between C _{SC} - COM	-0.3~V _{CC} +0.3	V

Total System

Symbol	Parameter	Conditions	Rating	Unit
V _{PN(PROT)}	Self Protection Supply Voltage Limit (Short Circuit Protection Capability)	$V_{CC} = V_{BS} = 13.5 \sim 16.5V$ $T_J = 125^{\circ}C$, Non-repetitive, less than $2\mu s$	400	V
T _C	Module Case Operation Temperature	-20°C≤ T _J ≤ 125°C, See Figure 2	-20 ~ 100	°C
T _{STG}	Storage Temperature		-40 ~ 125	°C
V _{ISO}	Isolation Voltage	60Hz, Sinusoidal, AC 1 minute, Connection Pins to ceramic substrate	2500	V _{rms}

Thermal Resistance

Symbol	Parameter	Conditios	Min.	Тур.	Max.	Unit
R _{th(j-c)Q}	Junction to Case Thermal	Inverter IGBT part (per 1/6 module)	-	-	3.1	°C/W
R _{th(j-c)F}	Resistance	Inverter FWD part (per 1/6 module)	-	-	3.6	°C/W

Note

2. For the measurement point of case temperature($T_{\mbox{\scriptsize C}}$), please refer to Figure 2.

^{1.} The maximum junction temperature rating of the power chips integrated within the Motion SPM® 3 Product is 150 °C(@T_C \leq 100°C). However, to insure safe operation of the Motion SPM 3 Product, the average junction temperature should be limited to $T_{J(ave)} \leq 125$ °C (@T_C \leq 100°C).

$\textbf{Electrical Characteristics} \ \, (T_J = 25^{\circ}\text{C}, \, \text{Unless Otherwise Specified})$

Inverter Part

S	ymbol	Item	Cond	lition	Min.	Тур.	Max.	Unit
V	CE(SAT)	Collector-Emitter Saturation Voltage	$V_{CC} = V_{BS} = 15V$ $V_{IN} = 5V$	I _C = 15A, T _J = 25°C	-	-	2.3	V
	V _F	FWD Forward Voltage	V _{IN} = 0V	I _C =15A, T _J = 25°C	-	-	2.1	V
HS	t _{ON}	Switching Times	V _{PN} = 300V, V _{CC} = V _{BS} = 15V		-	0.4	-	μS
	t _{C(ON)}		$I_C = 15A$ $V_{IN} = 0V \leftrightarrow 5V$, Induction	ive I nad	-	0.28	-	μS
	t _{OFF}		(Note 3)	1VC 2000	-	0.67	-	μS
	t _{C(OFF)}				-	0.35	-	μS
	t _{rr}				-	0.10	-	μS
LS	t _{ON}		$V_{PN} = 300V, V_{CC} = V_{B}$	_S = 15V	-	0.55	-	μS
	t _{C(ON)}		$I_C = 15A$ $V_{IN} = 0V \leftrightarrow 5V$, Induction	ive I and	-	0.24	-	μS
	t _{OFF}		(Note 3)	ive Load	-	0.73	-	μS
	t _{C(OFF)}				-	0.34	-	μS
	t _{rr}				-	0.10	-	μS
	I _{CES}	Collector-Emitter Leakage Current	V _{CE} = V _{CES}		-	1	250	μА

Note

^{3.} t_{ON} and t_{OFF} include the propagation delay time of the internal drive IC. $t_{C(ON)}$ and $t_{C(OFF)}$ are the switching time of IGBT itself under the given gate driving condition internally. For the detailed information, please see Figure 4.

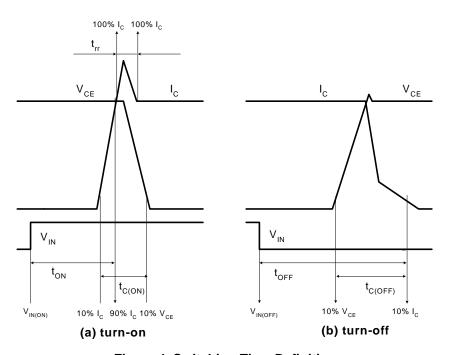


Figure 4. Switching Time Definition

$\textbf{Electrical Characteristics} \ \, (T_J = 25^{\circ}C, \, \text{Unless Otherwise Specified})$

Control Part

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
I _{QCCL}	Quiescent V _{CC} Supply Current	$V_{CC} = 15 \text{ V}$ $IN_{(UL, VL, WL)} = 0 \text{ V}$ $V_{CC(L)} - COM$	-	-	23	mA
I _{QCCH}		$ \begin{aligned} &V_{CC} = 1 \; 5V & V_{CC(UH)}, \; V_{CC(VH)}, \\ &IN_{(UH,\; VH,\; WH)} = 0 \; V & V_{CC(WH)} - COM \end{aligned} $	-	-	100	μΑ
I_{QBS}	Quiescent V _{BS} Supply Current	$ \begin{aligned} V_{BS} &= 15 \ V \\ IN_{(UH,\ VH,\ WH)} &= 0 \ V \end{aligned} \ \ \begin{aligned} V_{B(U)} &- V_{S(U)}, \ V_{B(V)} &- V_{S(V)} \\ V_{B(W)} &- V_{S(W)} \end{aligned} $		-	500	μΑ
V_{FOH}	Fault Output Voltage	V_{SC} = 0 V, V_{FO} Circuit: 4.7 k Ω to 5 V Pull-up	4.5	-	-	V
V_{FOL}		V_{SC} = 1 V, V_{FO} Circuit: 4.7 k Ω to 5 V Pull-up	-	-	0.8	V
V _{SC(ref)}	Short Circuit Trip Level	V _{CC} = 15 V (Note 4)	0.45	0.5	0.55	V
TSD	Over-temperature protection	Temperature at LVIC	125	145	175	°C
ΔTSD	Over-temperature protection hysterisis	Temperature at LVIC	-	18	-	°C
UV _{CCD}	Supply Circuit Under-	Detection Level	10.7	11.9	13.0	V
UV _{CCR}	Voltage Protection	Reset Level	11.2	12.4	13.2	V
UV _{BSD}		Detection Level	10.1	11.3	12.5	V
UV _{BSR}		Reset Level	10.5	11.7	12.9	V
t _{FOD}	Fault-out Pulse Width	C _{FOD} = 33nF (Note 5)	1.0	1.8	-	ms
V _{IN(ON)}	ON Threshold Voltage	Applied between IN _(UH) , IN _(VH) , IN _(WH) , IN _{(L}	_{JL)} , 3.0	-	-	V
V _{IN(OFF)}	OFF Threshold Voltage	IN _(VL) , IN _(WL) - COM	-	-	0.8	V

Note:

Recommended Operating Conditions

Symbol	Parameter	Conditions	Value			Unit
Symbol	raiailletei	Conditions	Min.	Тур.	Max.	Oilit
V _{PN}	Supply Voltage	Applied between P - N _U , N _V , N _W	-	300	400	V
V _{CC}	Control Supply Voltage	Applied between $V_{CC(UH)}$, $V_{CC(VH)}$, $V_{CC(WH)}$, $V_{CC(WH)}$,	13.5	15	16.5	V
V _{BS}	High-side Bias Voltage	Applied between $V_{B(U)}$ - $V_{S(U)}$, $V_{B(V)}$ - $V_{S(V)}$, $V_{B(W)}$ - $V_{S(W)}$	13.0	15	18.5	٧
DV _{CC} /Dt, DV _{BS} /Dt	Control supply variation		-1	-	1	V/μs
t _{dead}	Blanking Time for Preventing Arm-short	For Each Input Signal	2.0	-	-	μS
f _{PWM}	PWM Input Signal	$-20^{\circ}C \le T_{C} \le 100^{\circ}C, -20^{\circ}C \le T_{J} \le 125^{\circ}C$	-	-	20	kHz
V _{SEN}	Voltage for Current Sensing	Applied between N _U , N _V , N _W - COM (Including surge voltage)	-4		4	V

^{4.} Short-circuit current protection is functioning only at the low-sides.

^{5.} The fault-out pulse width t_{FOD} depends on the capacitance value of C_{FOD} according to the following approximate equation : $C_{FOD} = 18.3 \times 10^{-6} \times t_{FOD}[F]$

Mechanical Characteristics and Ratings

Parameter	Col	Limits			Unit	
Parameter	Col	Conditions			Max.	Onn
Mounting Torque	Mounting Screw: - M3	Recommended 0.62N•m	0.51	0.62	0.72	N•m
Device Flatness		Note Figure 5	0	-	+120	μ m
Weight			-	15.4	-	g

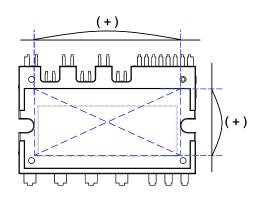
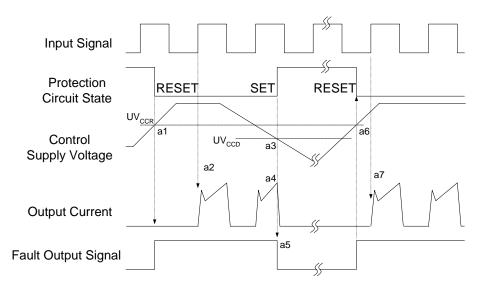


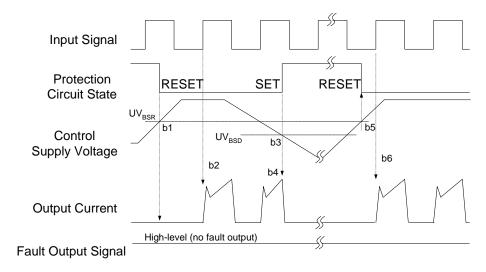
Figure 5. Flatness Measurement Position

Time Charts of Protective Function



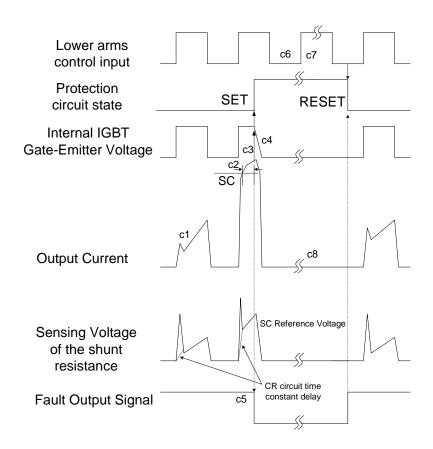
- a1 : Control supply voltage rises: After the voltage rises UV_{CCR} , the circuits start to operate when next input is applied.
- a2: Normal operation: IGBT ON and carrying current.
- a3 : Under voltage detection (UV_{CCD}).
- a4: IGBT OFF in spite of control input condition.
- a5 : Fault output operation starts.
- a6 : Under voltage reset (UV $_{CCR}$).
- a7: Normal operation: IGBT ON and carrying current.

Figure 6. Under-Voltage Protection (Low-side)



- b1 : Control supply voltage rises: After the voltage reaches UV_{BSR}, the circuits start to operate when next input is applied.
- b2: Normal operation: IGBT ON and carrying current.
- b3 : Under voltage detection (UV_{BSD}).
- b4: IGBT OFF in spite of control input condition, but there is no fault output signal.
- b5 : Under voltage reset (UV_{BSR})
- b6: Normal operation: IGBT ON and carrying current

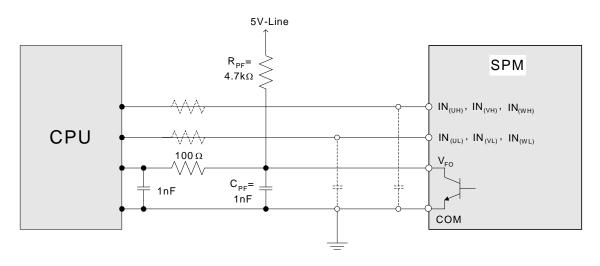
Figure 7. Under-Voltage Protection (High-side)



(with the external shunt resistance and CR connection)

- $\ensuremath{\text{c1}}$: Normal operation: IGBT ON and carrying current.
- $\ensuremath{\text{c2}}$: Short circuit current detection (SC trigger).
- c3: Hard IGBT gate interrupt.
- c4: IGBT turns OFF.
- c5 : Fault output timer operation starts: The pulse width of the fault output signal is set by the external capacitor C_{FO} .
- c6: Input "L": IGBT OFF state.
- c7 : Input "H": IGBT ON state, but during the active period of fault output the IGBT doesn't turn ON.
- c8: IGBT OFF state

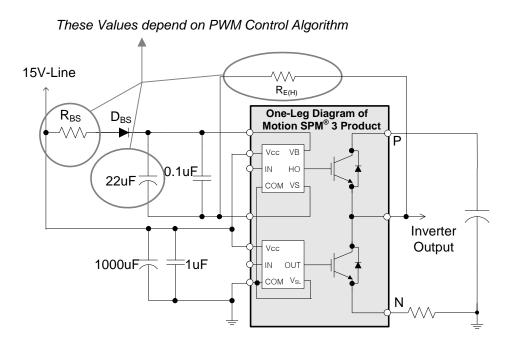
Figure 8. Short-Circuit Current Protection (Low-side Operation only)



Note:

- RC coupling at each input (parts shown dotted) might change depending on the PWM control scheme used in the application and the wiring impedance of the application's printed circuit board. The Motion SPM[®] 3 Product input signal section integrates 3.3kΩ (typ.) pull-down resistor. Therefore, when using an external filtering resistor, please pay attention to the signal voltage drop at input terminal.
- 2. The logic input is compatible with standard CMOS or LSTTL outputs.

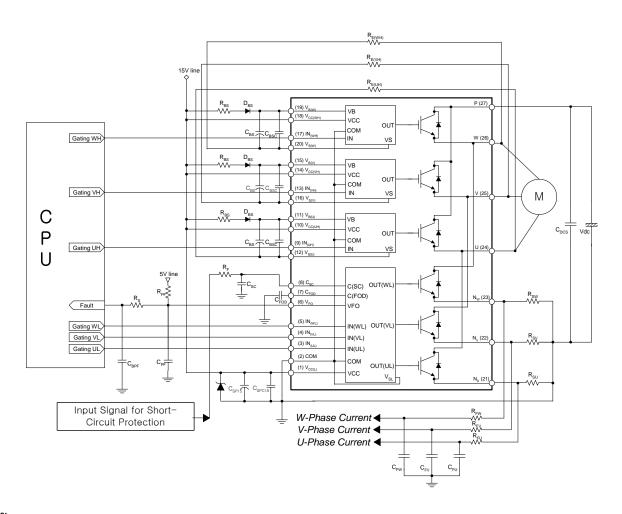
Figure 9. Recommended CPU I/O Interface Circuit



Note:

- 1. It would be recommended that the bootstrap diode, $D_{\mbox{\footnotesize{BS}}}$, has soft and fast recovery characteristics.
- 2. The bootstrap resistor (R_{BS}) should be 3 times greater than $R_{E(H)}$. The recommended value of $R_{E(H)}$ is 5.6 Ω , but it can be increased up to 20Ω (maximum) for a slower dv/dt of high-side.
- 3. The ceramic capacitor placed between V_{CC} -COM should be over 1uF and mounted as close to the pins of the Motion SPM 3 Product as possible.

Figure 10. Recommended Bootstrap Operation Circuit and Parameters

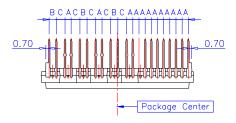


Note:

- 1. To avoid malfunction, the wiring of each input should be as short as possible. (less than 2-3cm)
- 2. By virtue of integrating an application specific type HVIC inside the Motion SPM[®] 3 Product, direct coupling to CPU terminals without any opto-coupler or transformer isolation is possible.
- $3.\ V_{FO}\ \text{output}\ \text{is open collector type.}\ \text{This signal line should be pulled up to the positive side of the 5V power supply}\ \ \text{with approximately } 4.7k\Omega\ \text{resistance}.\ \text{Please refer to Figure.}\ 9.$
- 4. $C_{\mbox{\footnotesize{SP15}}}$ of around 7 times larger than bootstrap capacitor $C_{\mbox{\footnotesize{BS}}}$ is recommended.
- 5. V_{FO} output pulse width should be determined by connecting an external capacitor(C_{FOD}) between C_{FOD}(pin7) and COM(pin2). (Example : if C_{FOD} = 33 nF, then t_{FO} = 1.8ms (typ.)) Please refer to the note 5 for calculation method.
- 6. Input signal is High-Active type. There is a 3.3kΩ resistor inside the IC to pull down each input signal line to GND. When employing RC coupling circuits, set up such RC couple that input signal agree with turn-off/turn-on threshold voltage.
- 7. To prevent errors of the protection function, the wiring around R_F and C_{SC} should be as short as possible.
- 8. In the short-circuit protection circuit, please select the $R_F C_{SC}$ time constant in the range 1.5~2 $\mu s.$
- 9. Each capacitor should be mounted as close to the pins of the Motion SPM 3 Product as possible.
- 10. To prevent surge destruction, the wiring between the smoothing capacitor and the P&GND pins should be as short as possible. The use of a high frequency non-inductive capacitor of around 0.1~0.22 uF between the P&GND pins is recommended.
- 11. Relays are used at almost every systems of electrical equipments of home appliances. In these cases, there should be sufficient distance between the CPU and the relays.
- 12. C_{SPC15} should be over 1uF and mounted as close to the pins of the Motion SPM 3 Product as possible.

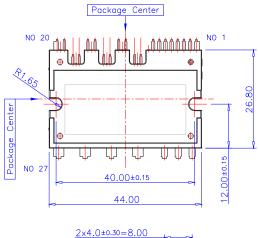
Figure 11. Typical Application Circuit

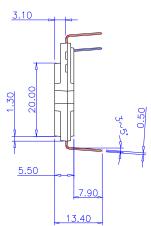
Detailed Package Outline Drawings

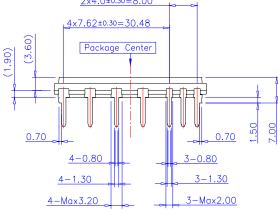


Lead Pitch : ±0.30

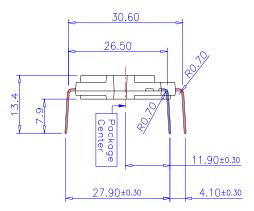
A: 1.778 B: 2.050 C: 2.531



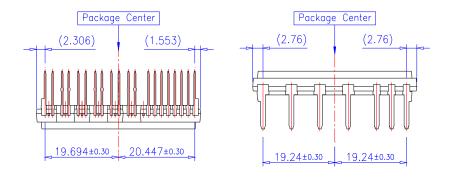




Detailed Package Outline Drawings (Continued)

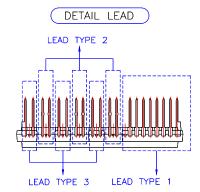


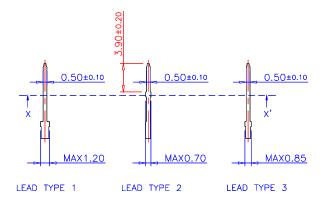
Lead Forming Dimension

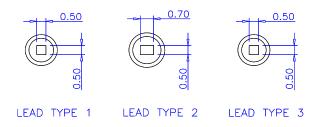


PKG Center to Lead Distance

Detailed Package Outline Drawings (Continued)







LEAD SECTION X-X'





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ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufacturers of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed applications, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handling and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will standards for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition		
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.		
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.		
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.		
Obsolete Not In Production		Datasheet contains specifications on a product that is discontinued by Fairchild Semiconduc The datasheet is for reference information only.		

Rev 164

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